

NPN switching transistor

PXT3904

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 40 V).

APPLICATIONS

- High-speed switching.

DESCRIPTION

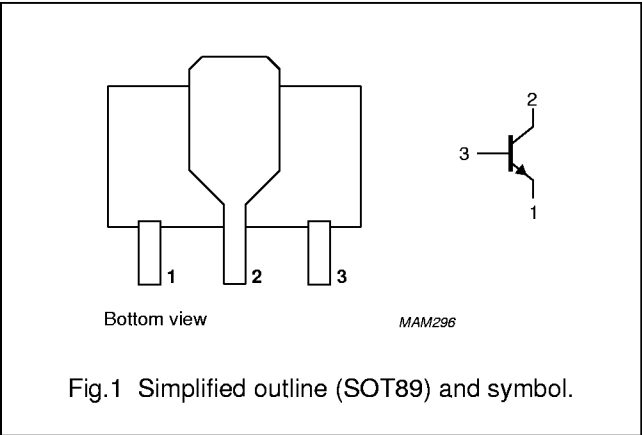
NPN switching transistor in a SOT89 plastic package.
PNP complement: PXT3906.

MARKING

TYPE NUMBER	MARKING CODE
PXT3904	p1A

PINNING

PIN	DESCRIPTION
1	emitter
2	collector
3	base



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	—	60	V
V_{CEO}	collector-emitter voltage	open base	—	40	V
V_{EBO}	emitter-base voltage	open collector	—	6	V
I_C	collector current (DC)		—	100	mA
I_{CM}	peak collector current		—	200	mA
I_{BM}	peak base current		—	100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^{\circ}\text{C}$; note 1	—	1.2	W
T_{stg}	storage temperature		−55	+150	$^{\circ}\text{C}$
T_j	junction temperature		—	150	$^{\circ}\text{C}$
T_{amb}	operating ambient temperature		−55	+150	$^{\circ}\text{C}$

Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 6 cm².
For other mounting conditions, see “Thermal considerations for SOT89 in the General Part of associated Handbook”.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	105	K/W
$R_{th\ j-s}$	thermal resistance from junction to soldering point		25	K/W

Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 6 cm².
For other mounting conditions, see "Thermal considerations for SOT89 in the General Part of associated Handbook".

CHARACTERISTICS

$T_j = 25\ ^\circ\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = 30\text{ V}$	–	50	nA
I_{EBO}	emitter cut-off current	$I_C = 0$; $V_{EB} = 6\text{ V}$	–	50	nA
h_{FE}	DC current gain	$V_{CE} = 1\text{ V}$; (see Fig.2) $I_C = 0.1\text{ mA}$ $I_C = 1\text{ mA}$ $I_C = 10\text{ mA}$ $I_C = 50\text{ mA}$ $I_C = 100\text{ mA}$	60 80 100 60 30	– – 300 – –	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA}$; $I_B = 1\text{ mA}$	–	200	mV
		$I_C = 50\text{ mA}$; $I_B = 5\text{ mA}$	–	200	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 10\text{ mA}$; $I_B = 1\text{ mA}$	650	850	mV
		$I_C = 50\text{ mA}$; $I_B = 5\text{ mA}$	–	950	mV
C_c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = 5\text{ V}$; $f = 1\text{ MHz}$	–	4	pF
C_e	emitter capacitance	$I_C = i_c = 0$; $V_{EB} = 500\text{ mV}$; $f = 1\text{ MHz}$	–	8	pF
f_T	transition frequency	$I_C = 10\text{ mA}$; $V_{CE} = 20\text{ V}$; $f = 100\text{ MHz}$	300	–	MHz
F	noise figure	$I_C = 100\ \mu\text{A}$; $V_{CE} = 5\text{ V}$; $R_S = 1\text{ k}\Omega$; $f = 10\text{ Hz}$ to 15.7 kHz	–	5	dB
Switching times (between 10% and 90% levels); (see Fig.3)					
t_{on}	turn-on time	$I_{Con} = 10\text{ mA}$; $I_{Bon} = 1\text{ mA}$; $I_{Boff} = -1\text{ mA}$	–	65	ns
t_d	delay time		–	35	ns
t_r	rise time		–	35	ns
t_{off}	turn-off time		–	240	ns
t_s	storage time		–	200	ns
t_f	fall time		–	50	ns

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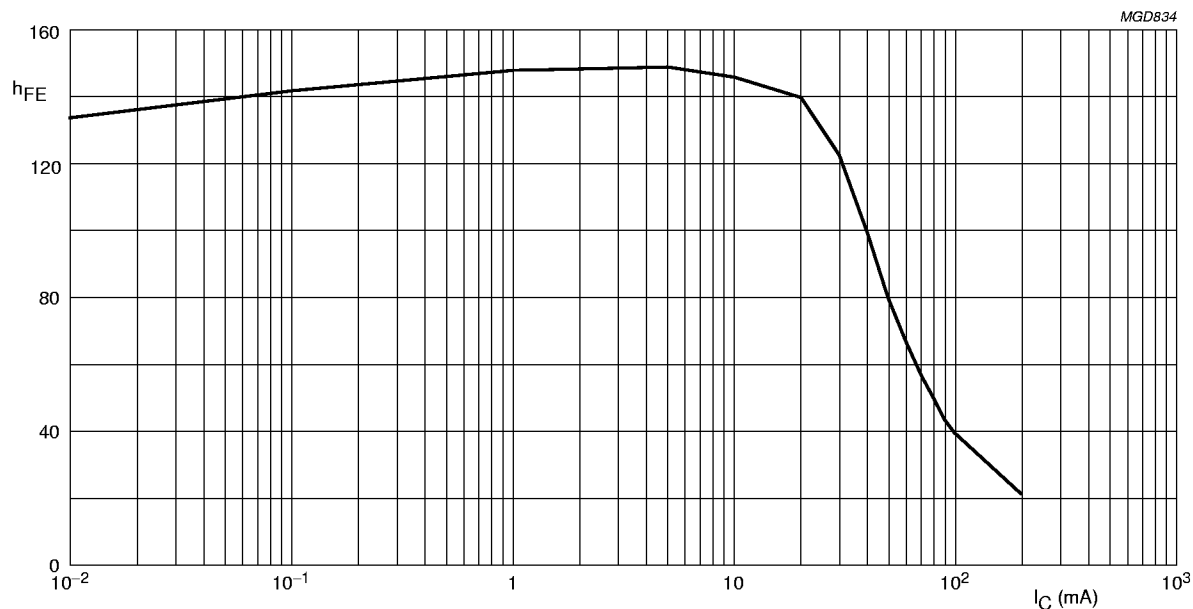
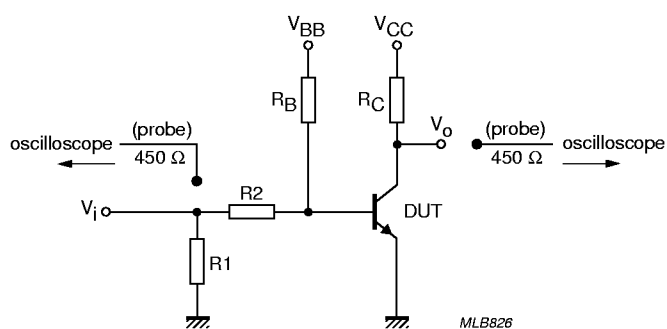
 $V_{CE} = 1 \text{ V.}$

Fig.2 DC current gain; typical values.



$V_i = 5 \text{ V; } T = 500 \text{ } \mu\text{s; } t_p = 10 \text{ } \mu\text{s; } t_r = t_f \leq 3 \text{ ns.}$
 $R_1 = 56 \text{ } \Omega; R_2 = 2.5 \text{ k}\Omega; R_B = 3.9 \text{ k}\Omega; R_C = 270 \text{ } \Omega.$
 $V_{BB} = 1.9 \text{ V; } V_{CC} = -3 \text{ V.}$
 Oscilloscope: input impedance $Z_i = 50 \text{ } \Omega.$

Fig.3 Test circuit for switching times.

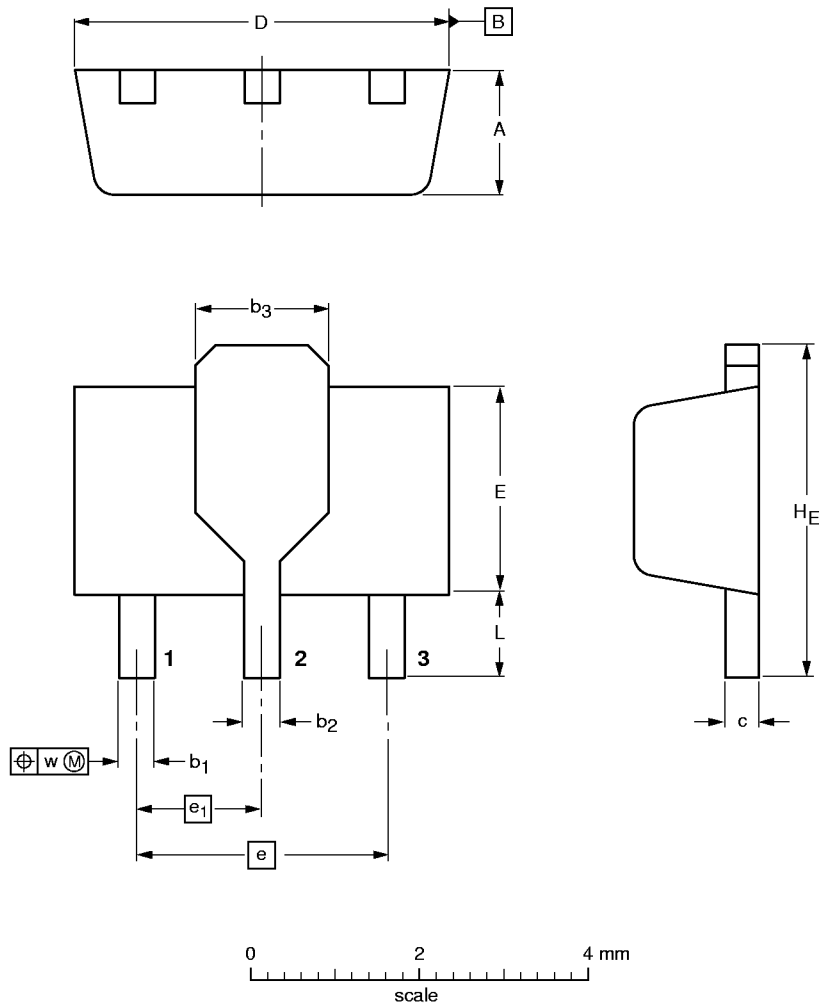
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PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 3 leads

SOT89



DIMENSIONS (mm are the original dimensions)

UNIT	A	b ₁	b ₂	b ₃	c	D	E	e	e ₁	H _E	L min.	w
mm	1.6 1.4	0.48 0.35	0.53 0.40	1.8 1.4	0.44 0.37	4.6 4.4	2.6 2.4	3.0	1.5	4.25 3.75	0.8	0.13

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT89						97-02-28